

Description

Features

- 20V, 6.0A
- $R_{DS(on)Typ} = 20m\Omega @ V_{GS} = 4.5V$
- $R_{DS(on)Typ} = 27m\Omega @ V_{GS} = 2.5V$
- Very Low On-resistance $R_{DS(on)}$
- Improved dv/dt capability
- Low C_{rss}

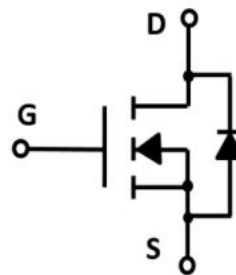
Application

- PWM Application
- Load Switch
- Power Management

Package



SOP-8



Schematic diagram

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	SLV2302A	Units
V_{DSS}	Drain-Source Voltage	20	V
I_D	Drain Current- Continuous ($T_C = 25^\circ C$)	6.0	A
	- Continuous ($T_C = 70^\circ C$)	4.5	A
I_{DM}	Drain Current - Pulsed (Note 1)	24	A
V_{GSS}	Gate-Source Voltage	± 10	V
P_D	Power Dissipation ($T_C = 25^\circ C$)	2.0	W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	68.5	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel
9926A/M	9926	SOP-8	4000

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±10V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	0.45	-	1.1	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =4.5V, I _D =4.3A	-	20	27	mΩ
		V _{GS} =2.5V, I _D =3.0A	-	27	38	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =20A	-	24.6	-	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f = 1.0MHz	-	468	-	pF
C _{oss}	Output Capacitance		-	87	-	pF
C _{rss}	Reverse Transfer Capacitance		-	76	-	pF
R _g	Gate resistance	-	-	-	-	Ω
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =4.3A, V _{GS} =5V	-	8.4	-	nC
Q _{gs}	Gate-Source Charge		-	0.8	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.9	-	nC
V _{plateau}	Gate plateau voltage		-	-	-	V
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, V _{GS} =5V R _L =2.7Ω, R _{GEN} =6Ω	-	5.2	-	ns
t _r	Turn-on Rise Time		-	37	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	5.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _s =10A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, R_G=25\Omega, L=0.5mH$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

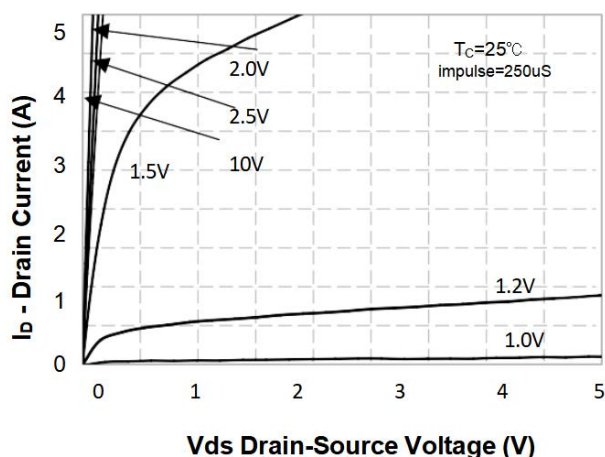


Figure 1. On-Region Characteristics

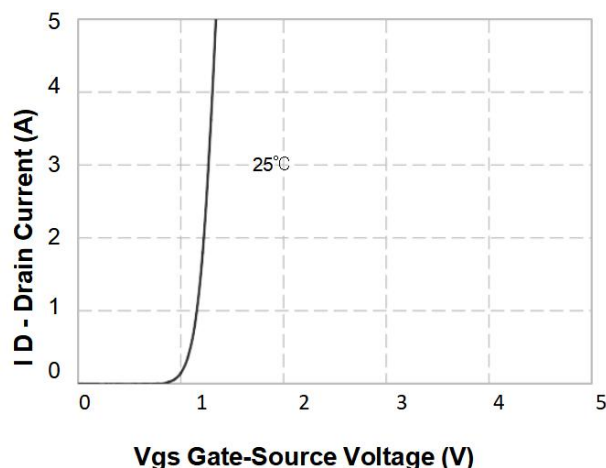


Figure 2. Transfer Characteristics

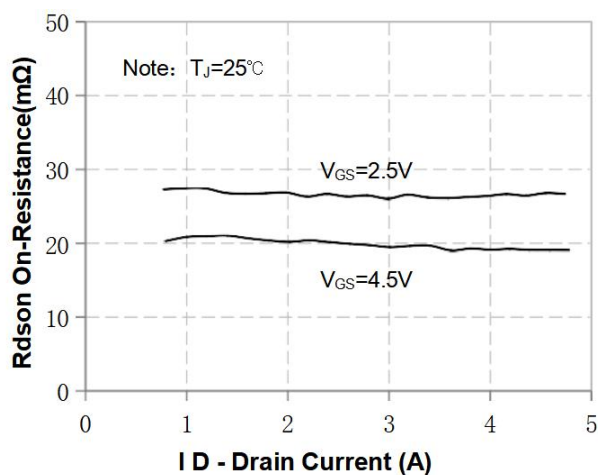


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

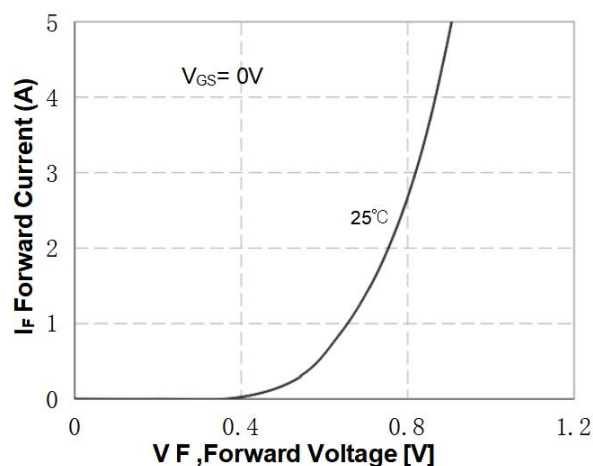


Figure 4. Body Diode Forward Voltage Variation with Source Current

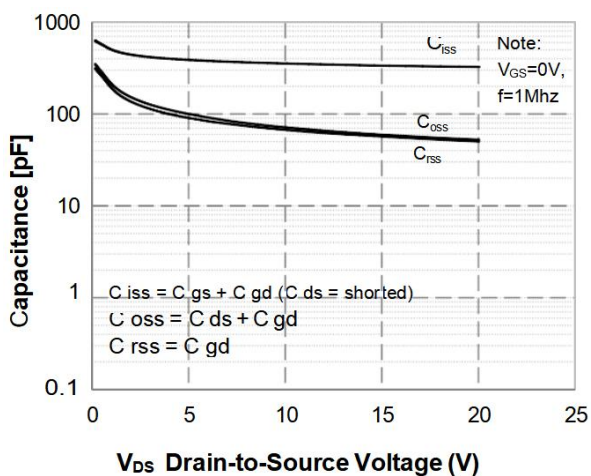


Figure 5. Capacitance Characteristics

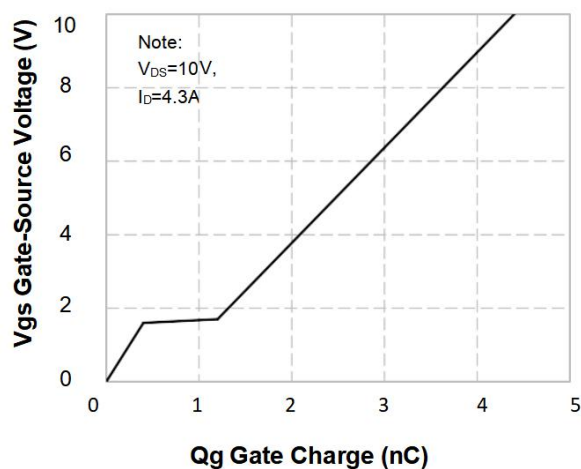


Figure 6. Gate Charge Characteristics

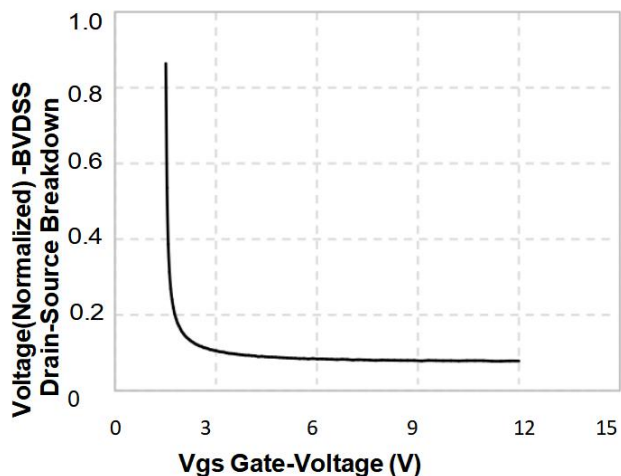


Figure 7. Breakdown Voltage Variation vs Gate-Voltage

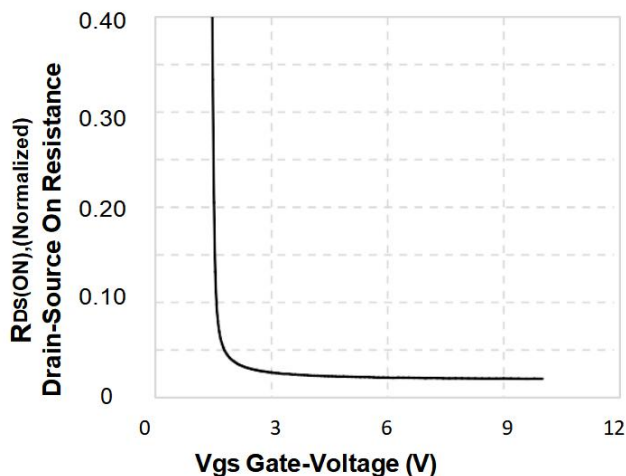


Figure 8. On-Resistance Variation vs Gate Voltage

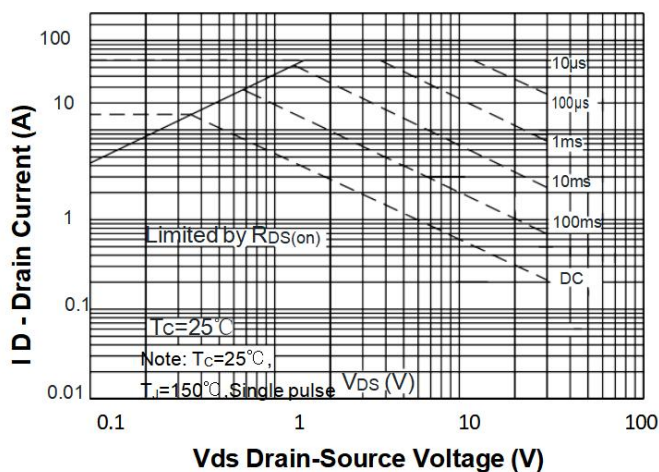


Figure 9. Maximum Safe Operating Area

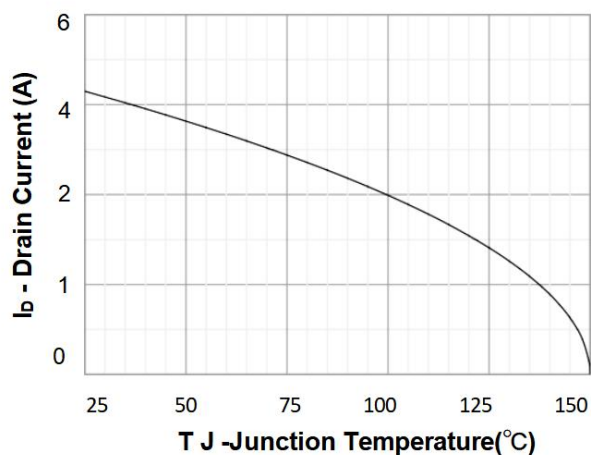


Figure 10. Maximum Continuous Drain Current vs Temperature

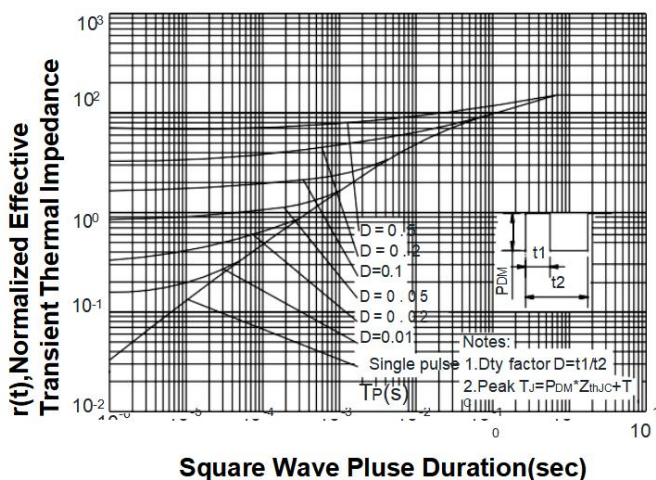
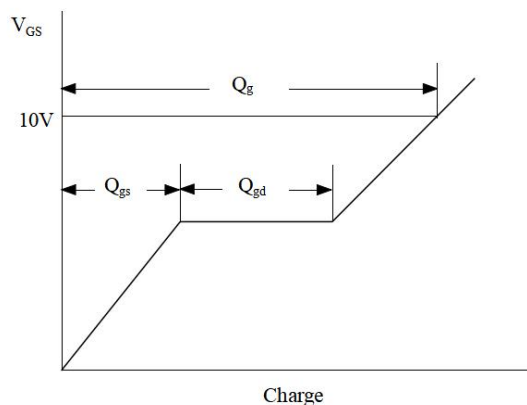
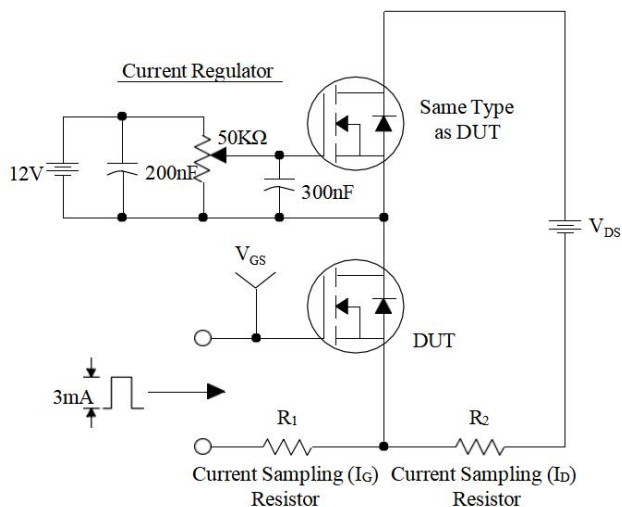


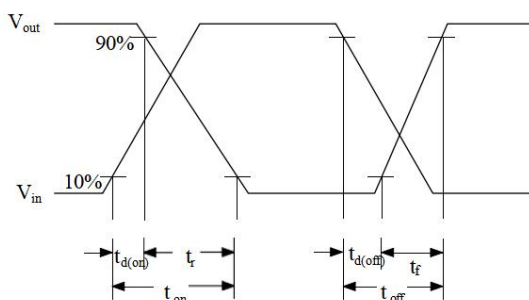
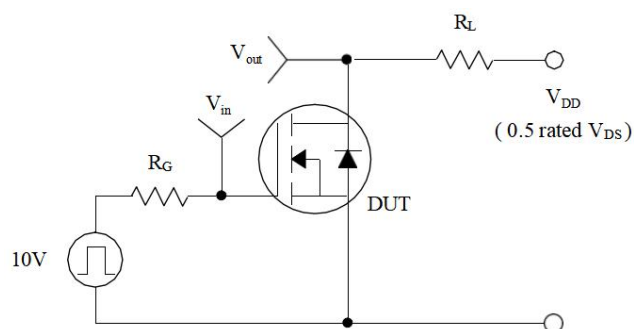
Figure 11. Transient Thermal Response Curve

Test Circuit

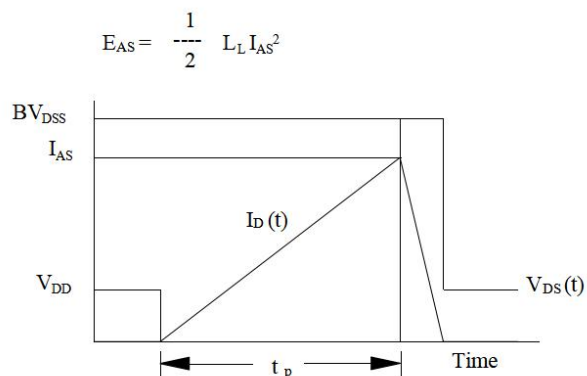
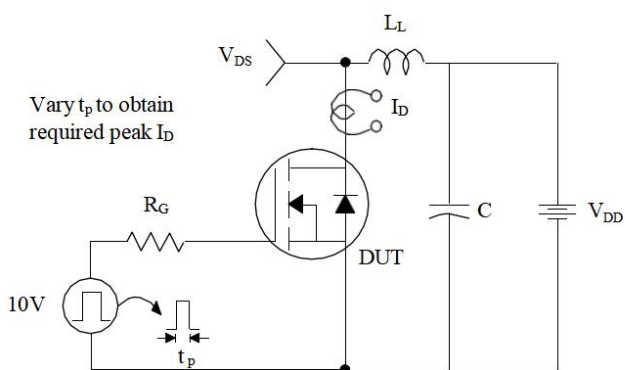
Gate Charge Test Circuit & Waveform



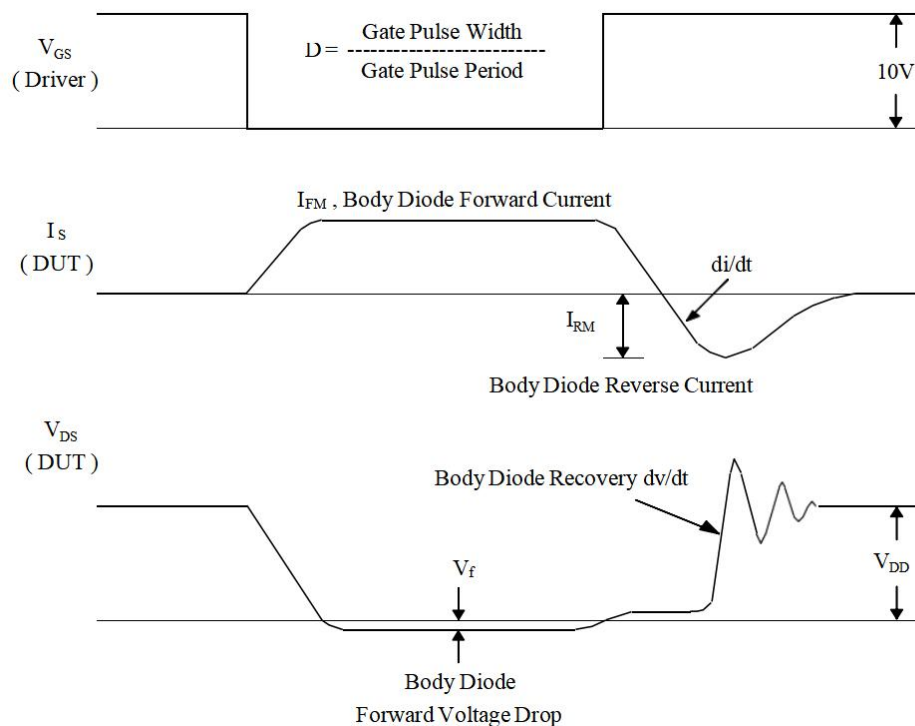
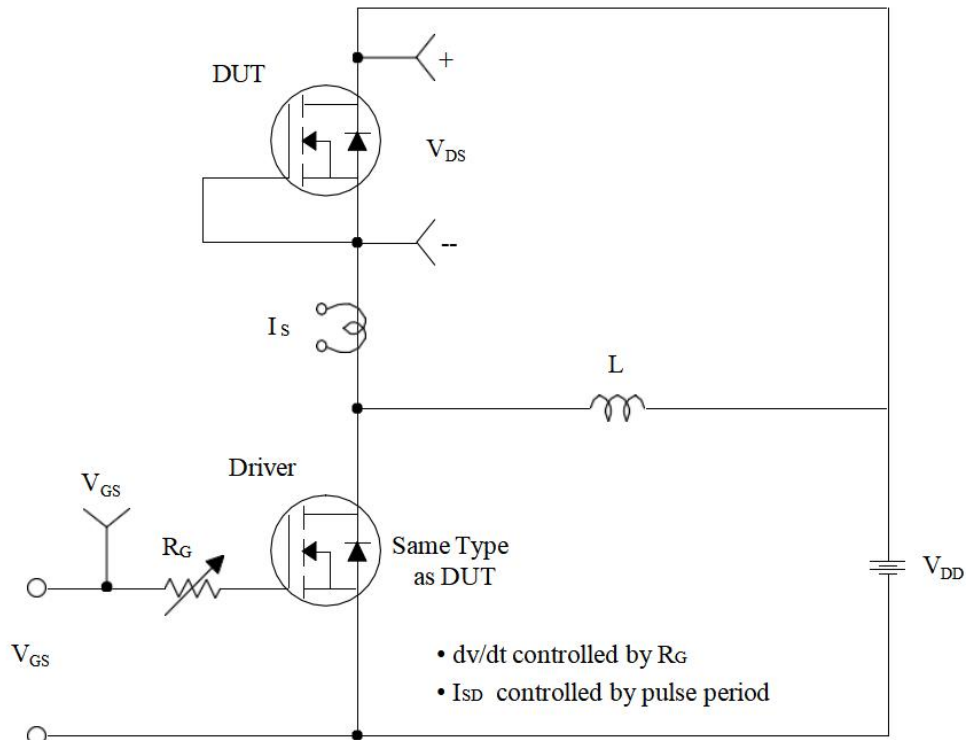
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

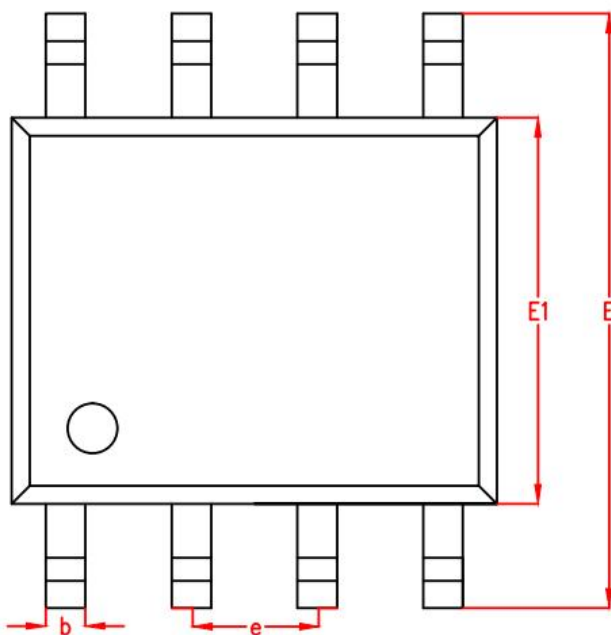
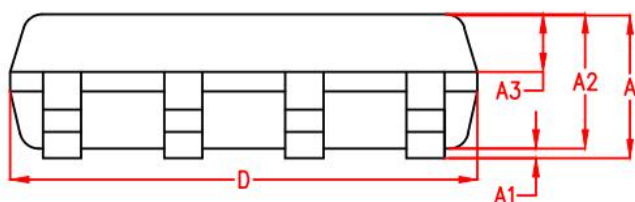
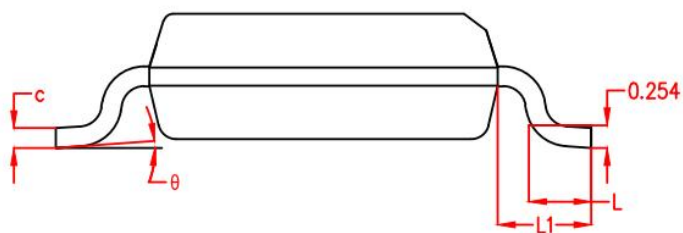


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Information

➤ SOP-8



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.38	1.50	1.60
A1	0.03	0.10	0.15
A2	1.35	1.40	1.45
A3	0.55	0.60	0.65
b	0.35	0.40	0.45
c	0.19	0.22	0.25
D	4.85	4.90	4.95
E	5.80	6.00	6.20
E1	3.85	3.90	3.95
e	1.27BSC		
L	0.45	0.60	0.75
L1	1.05BSC		
θ	0°	4°	8°